

KST5551

- Amplifier Transistor

 Collector-Emitter Voltage: V_{CEO}=160V

 Collector Power Dissipation: P_C (max)=350mW



1. Base 2. Emitter 3. Collector

Rev. B2, February 2003

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	180	V
V _{CEO}	Collector-Emitter Voltage	160	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	600	mA
P _C	Collector Power Dissipation	350	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Refer to 2N5551 for graphs

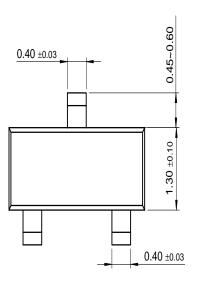
Electrical Characteristics T_a=25°C unless otherwise noted

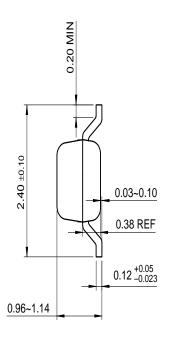
Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =100μA, I _E =0	180		V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =1mA, I _B =0	160		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =10μA, I _C =0	6		V
I _{CBO}	Collector Cut-off Current	V _{CB} =120V, I _E =0		50	nA
I _{EBO}	Emitter Cut-off Current	V_{EB} =4V, I_{C} =0		50	nA
h _{FE}	DC Current Gain	V_{CE} =5V, I_{C} =1mA V_{CE} =5V, I_{C} =10mA V_{CE} =5V, I_{C} =50mA	80 80 30	250	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I_C =10mA, I_B =1mA I_C =50mA, I_B =5mA		0.15 0.2	V V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I_C =10mA, I_B =1mA I_C =50mA, I_B =5mA		1 1	V V
f _T	Current Gain Bandwidth Product	V _{CE} =10V, I _C =10mA, f=100MHz	100	300	MHz
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0, f=1MHz		6	pF
NF	Noise Figure	V_{CE} =5V, I_{C} =250μA, R_{S} =1KΩ, I_{CE} =10Hz to 15.7KMz		8	dB

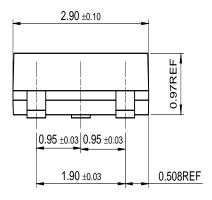
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Package Dimensions

SOT-23







Dimensions in Millimeters

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Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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